查询LLSD101供应商

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LLSD101A THRU LLSD101C

Schottky Barrier Switching Diode

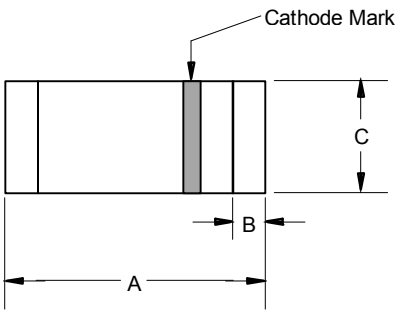
Features

- Low Reverse Recovery Time
- Low Reverse Capacitance
- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection

Mechanical Data

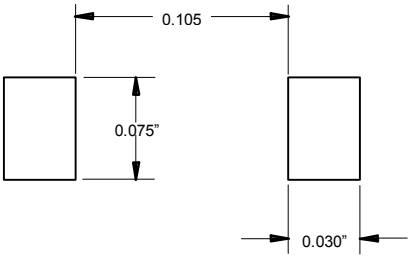
- Case: MiniMELF, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Indicated by Cathode Band
- Weight: 0.05 grams (approx.)

MINIMELF



DIMENSION					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.134	.142	3.40	3.60	
B	.008	.016	.20	.40	
C	.055	.059	1.40	1.50	

SUGGESTED SOLDER PAD LAYOUT



Maximum Ratings @ 25°C Unless Otherwise Specified

Characteristic	Symbol	LLSD101A	LLSD101B	LLSD101C
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	60V	50V	40V
RMS Reverse Voltage	$V_{R(RMS)}$	42V	35V	28V
Forward Continuous Current(Note 1)	I_{FM}	15mA		
Non-Repetitive Peak @ t<=1.0s Forward Surge Current @ t=10us	I_{FSM}	50mA 2.0A		
Power Dissipation(Note 1)	Pd	400mW		
Thermal Resistance(Note 1)	R	375K/W		
Operation & Storage Temp. Range	Tj, T_{STG}	-55 to 150°C		

Electrical Characteristics @ 25°C Unless Otherwise Specified

Charateristic		Symbol	Min	Max	Unit	Test Cond.
Peak Reverse Current	LLSD101A	I_{RM}	-----	200	nA	V_R=50V
	LLSD101B					V_R=40V
	LLSD101C					V_R=30V
Forward Volt. Drop	LLSD101A	V_{FM}	-----	0.41	V	I_F=1.0mA
	LLSD101B			0.40		I_F=1.0mA
	LLSD101C			0.39		I_F=1.0mA
	LLSD101A			1.00		I_F=15mA
	LLSD101B			0.95		I_F=15mA
	LLSD101C			0.90		I_F=15mA
Junction Capacitance	LLSD101A	Cj	-----	2.0	pF	V_R=0V, f=1.0MHz
	LLSD101B			2.1		
	LLSD101C			2.2		
Reverse Recovery Time		t_{rr}	-----	1.0	ns	I_F=I_R=5mA, recover to 0.1 I_R

Note: 1. Valid provided that electrodes are kept at ambient temperature

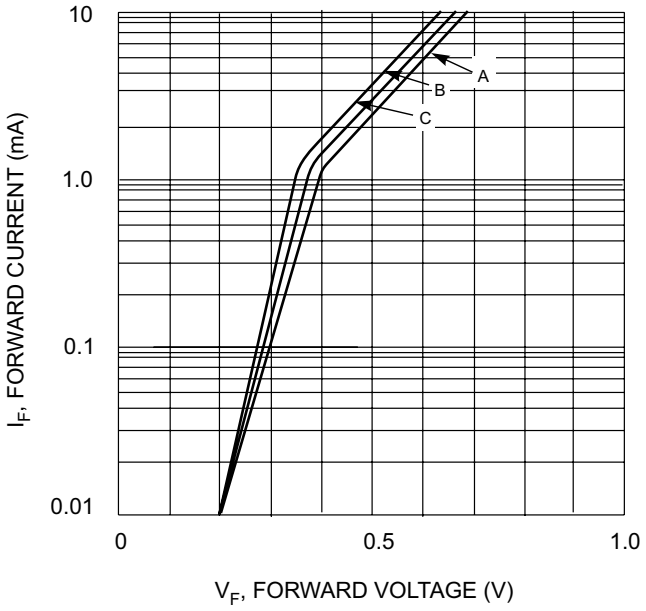


Fig. 1 Typical Forward Characteristic Variations for Primary Conduction

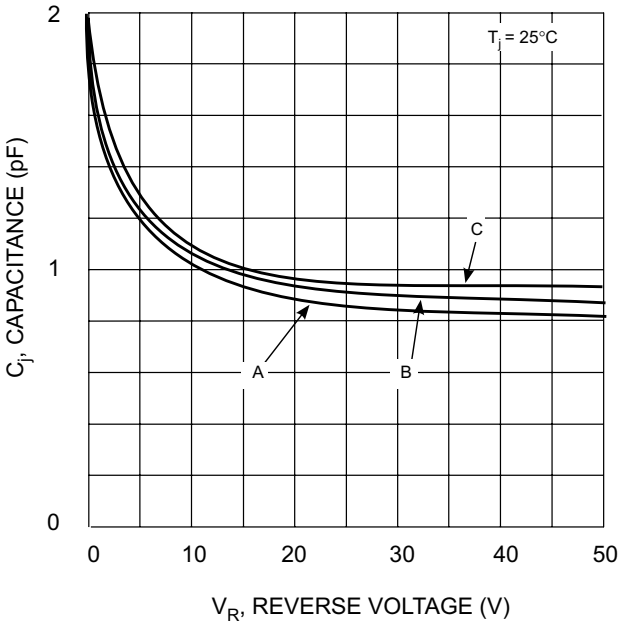


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage